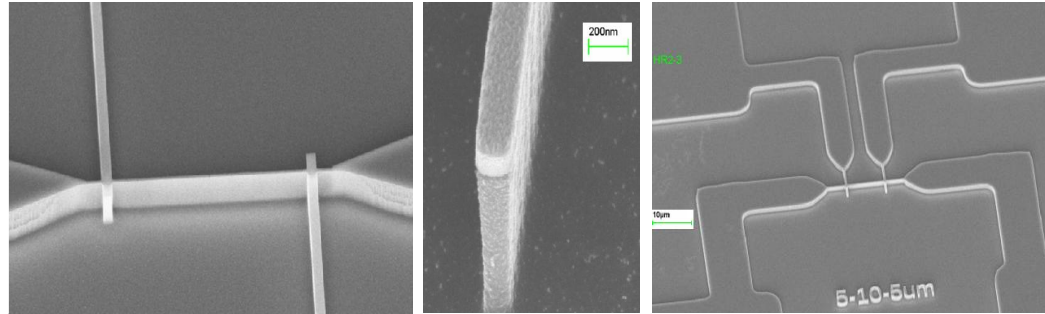




Effect of phonon confinement on heat dissipation in ridges

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- **Phonon transport confinement effects**

- Measuring the temperature in ridge samples
- Thermal conductance of silicon ridges
- Conclusion/Perspectives

Phonon transport confinement effects

Phonon lengthscales

- Acoustic phonons are the main heat carriers in nonmetals

Thermal
wavelengths

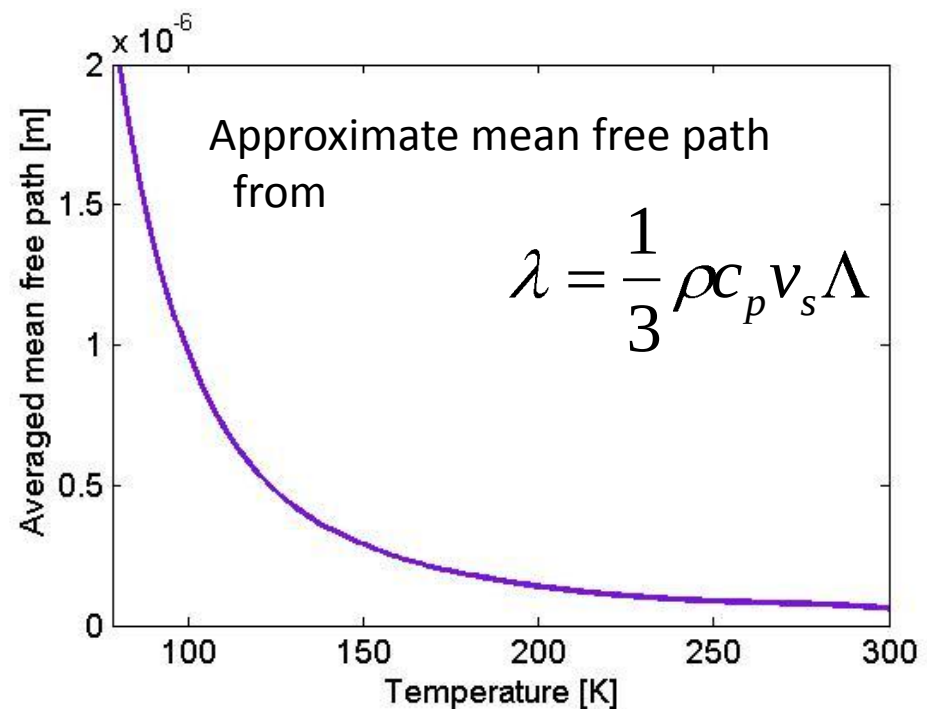
[~0 - 20] nm

@RT

Mean free path
(MFP)

[10 – 500] nm

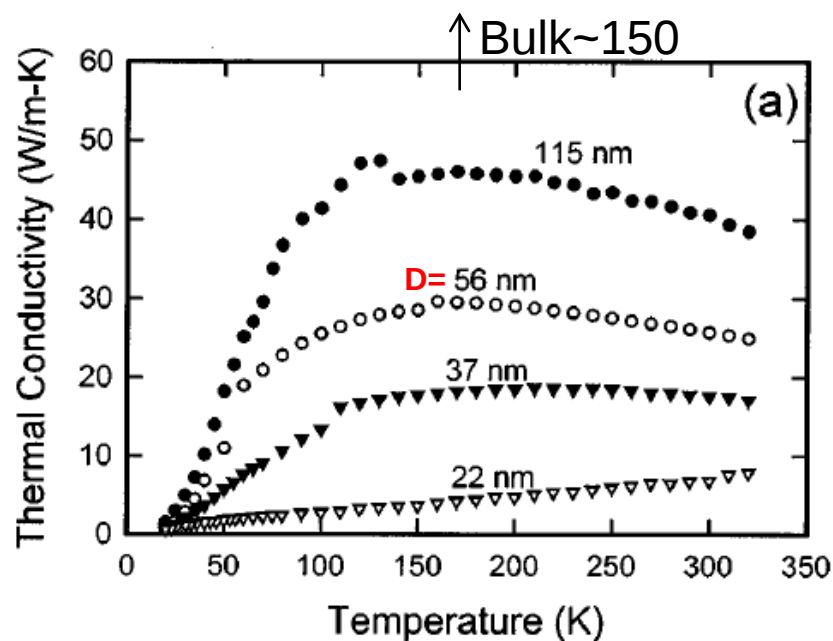
=f(ω)



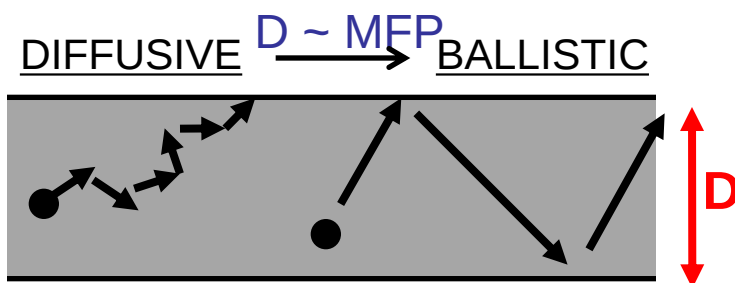
- Vary temperature to change the average MFP

Phonon transport confinement effects

Example: suspended nanowires



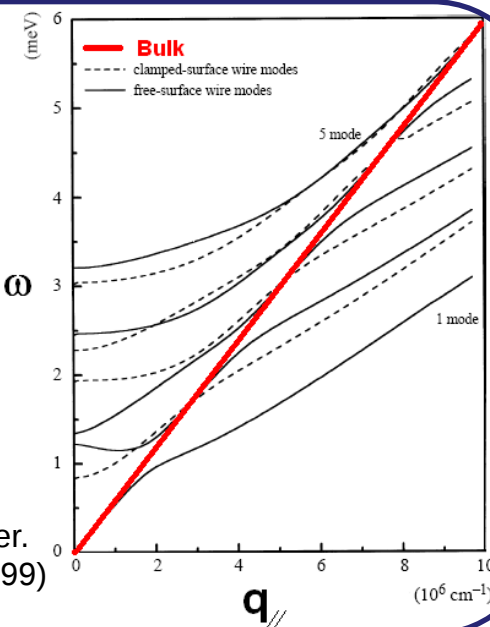
Li, ..., Majumdar, Appl. Phys. Lett. 83, 2934 (2003)



Particle

Wave ?

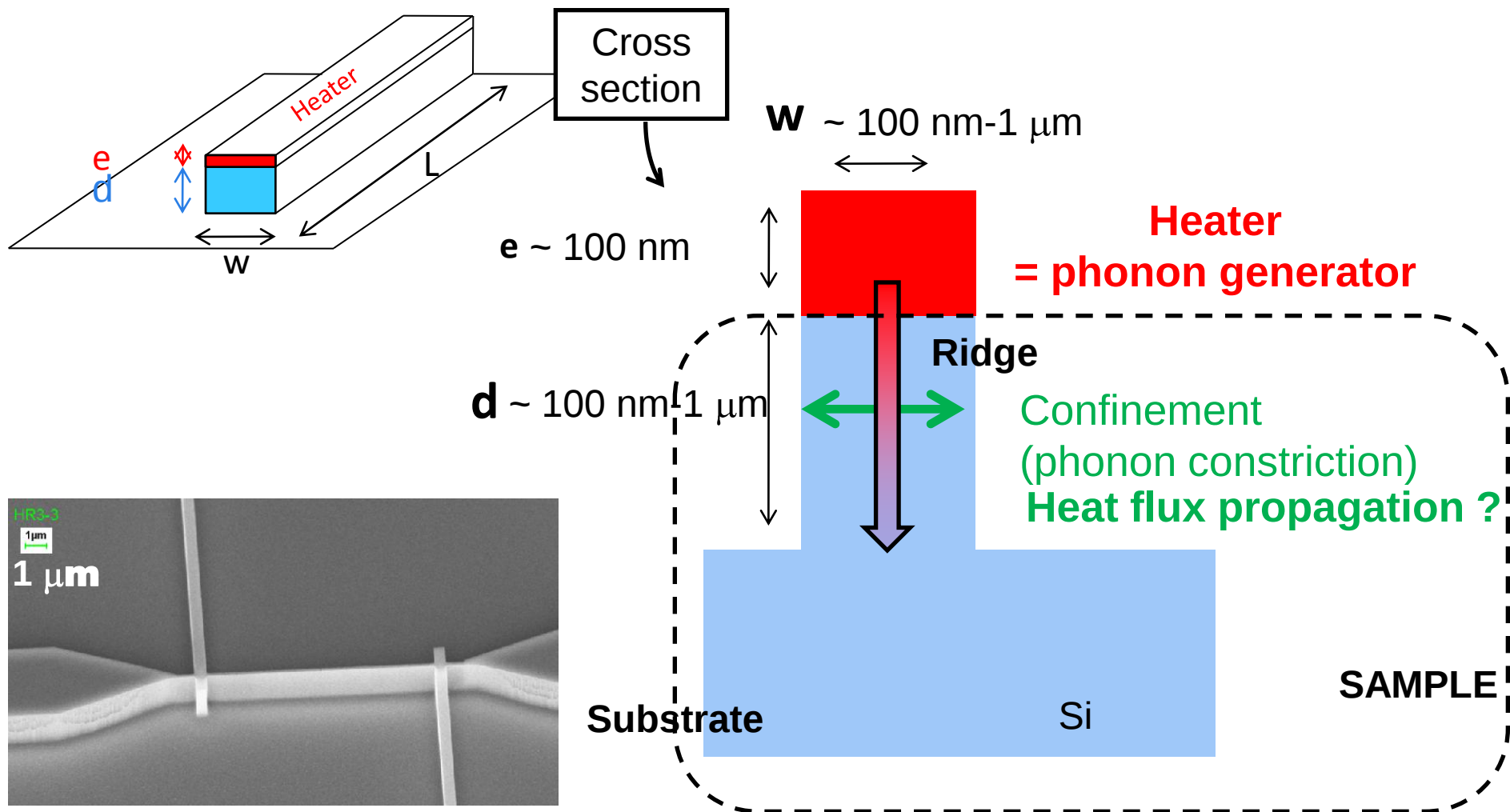
Change in
dispersion
relation



Balandin, J. Super. Micro 26, 181 (1999)

Phonon transport confinement effects

Supported nanostructures



- Phonon transport confinement effects
- **Measuring the temperature in ridge samples**
- Thermal conductance of silicon ridges
- Conclusion/Perspectives

Measuring the ridge temperature

Wire temperature measurement

3ω method, Cahill, RSI (1990)

- $R(T) = R_0 (1 + \alpha \Delta T)$

Resistance depends on temperature

- $I = I_\omega \cos(\omega t)$

$$\rightarrow P(t) = R I(t)^2 = \frac{1}{2} R_0 (1 + \cos(2\omega t))$$

$$\rightarrow T(t) = T_0 + T_{DC} + T_{2\omega} \cos(2\omega t + \phi_{2\omega})$$

Joule heating of the electric wire

$$\begin{aligned} U &= RI = R_0 [1 + \alpha(T_{DC} + T_{2\omega} \cos(2\omega t + \phi_{2\omega}))] I_\omega \cos(\omega t) \\ &= R_0 I_\omega [(1 + \alpha T_{DC}) \cos(\omega t) + \frac{1}{2} \alpha T_{2\omega} \cos(\omega t - \phi_{2\omega}) + \frac{1}{2} \alpha T_{2\omega} \cos(3\omega t + \phi_{2\omega})] \\ &= U_{1\omega} + \frac{1}{2} \alpha R_0 I_\omega T_{2\omega} \cos(3\omega t + \phi_{2\omega}) \end{aligned}$$



Lock-in
detection

- Other possibility: Combining DC and AC current input

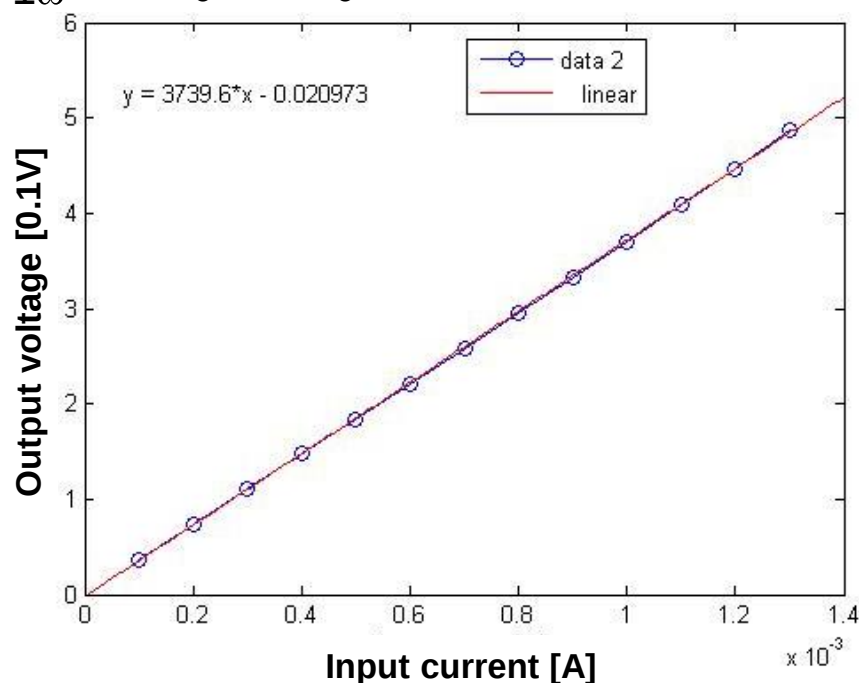
$$I = I_0 + I_\omega \cos(\omega t) \longrightarrow U_\omega = R_0 I_\omega (1 + \alpha T_{DC}) \cos(\omega t)$$

- Wire temperature = f (heat flux in the sample)

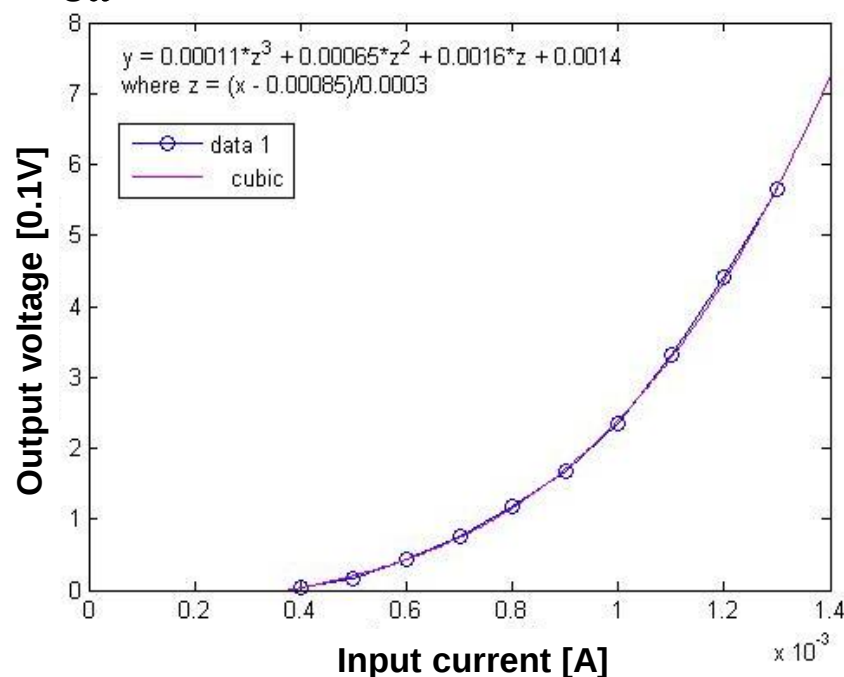
Measuring the ridge temperature

Wire temperature measurement

$$V_{1\omega} = R_0 I \sim R_0$$



$$V_{3\omega} \sim I^3$$



Measuring the ridge temperature

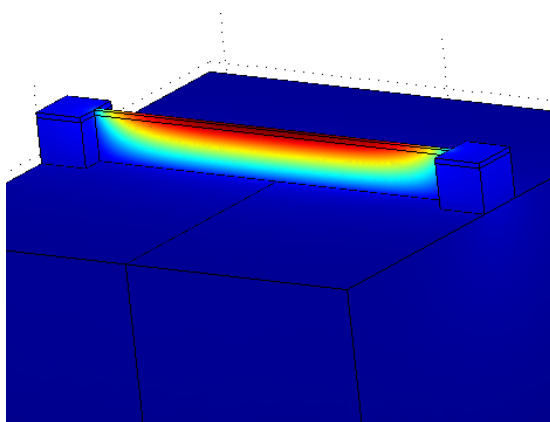
Calculation of the conductance G_{th}

- The conductance is obtained from
- $F_{geometry}$? take $F = 1$ as upper limit
- Pads are heat baths. T_{wire} is not constant along its length.

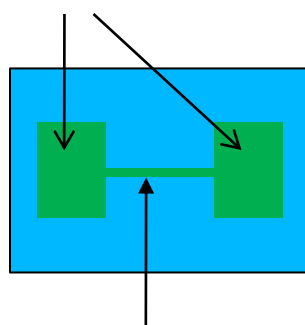
$$G_{th} = P / \Delta T$$

$$= F_{geometry} R I^2 / \Delta T$$

Temperature
distribution



FEM simulation

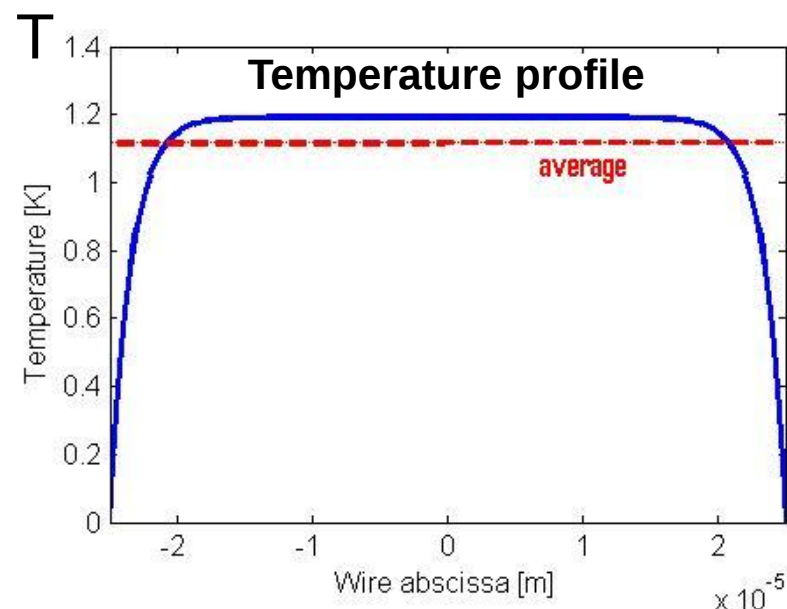


wire

$$I_0 = 1.3 \cdot 10^{-3} \text{ A}$$

$$g = 10^8 \text{ WK}^{-1}\text{m}^{-2}$$

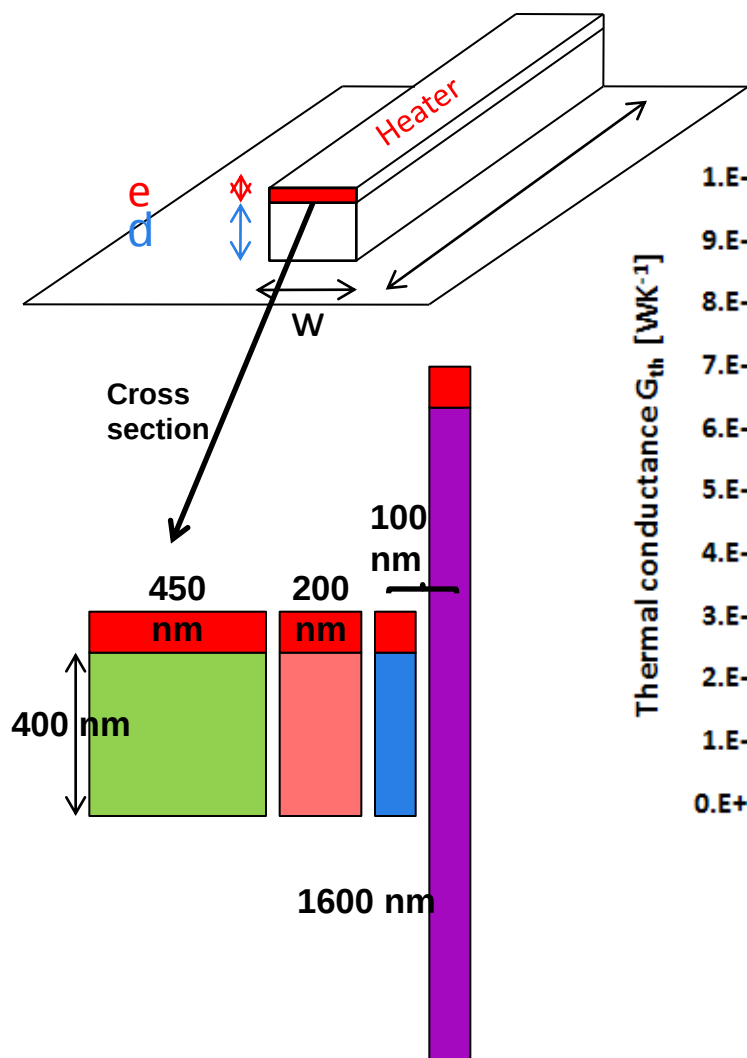
$$(f = 12 \text{ Hz})$$



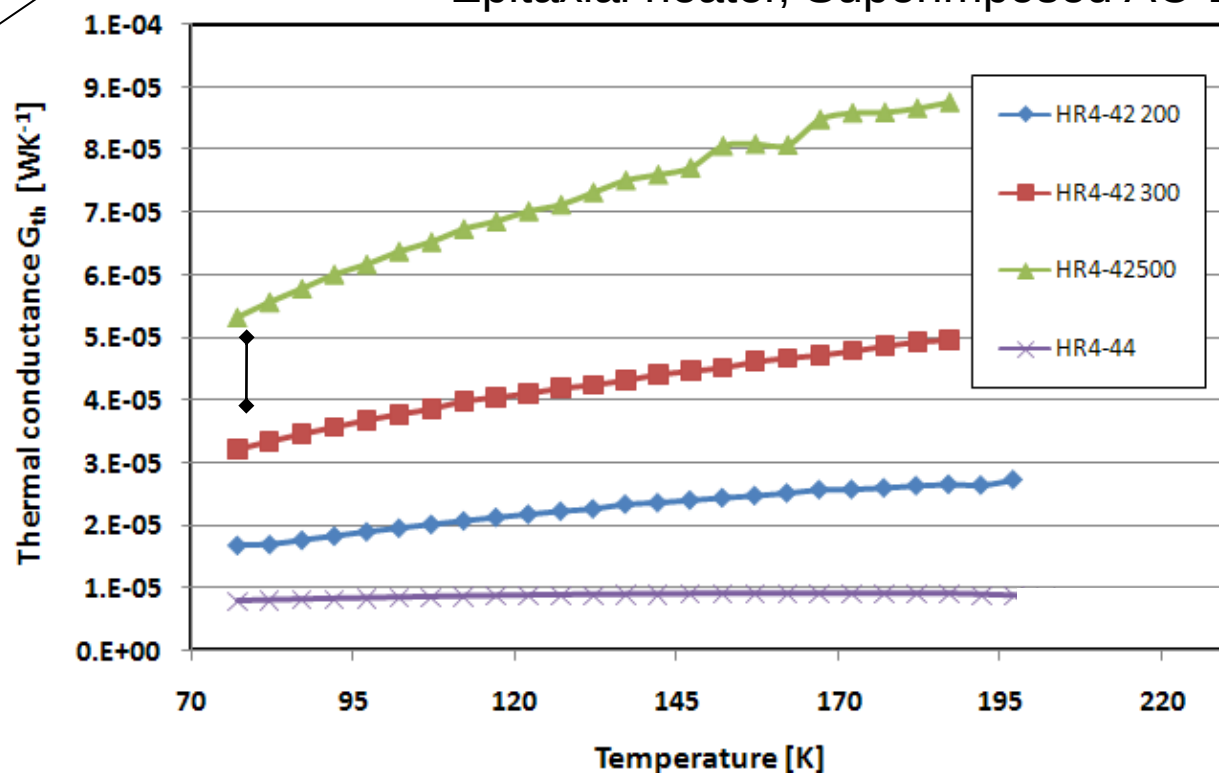
Analytical calculation

- Phonon transport confinement effects
- Measuring the temperature in ridge samples
- **Thermal conductance of silicon ridges**
- Conclusion/Perspectives

Thermal conductances of Si ridges



Epitaxial heater, Superimposed AC-DC

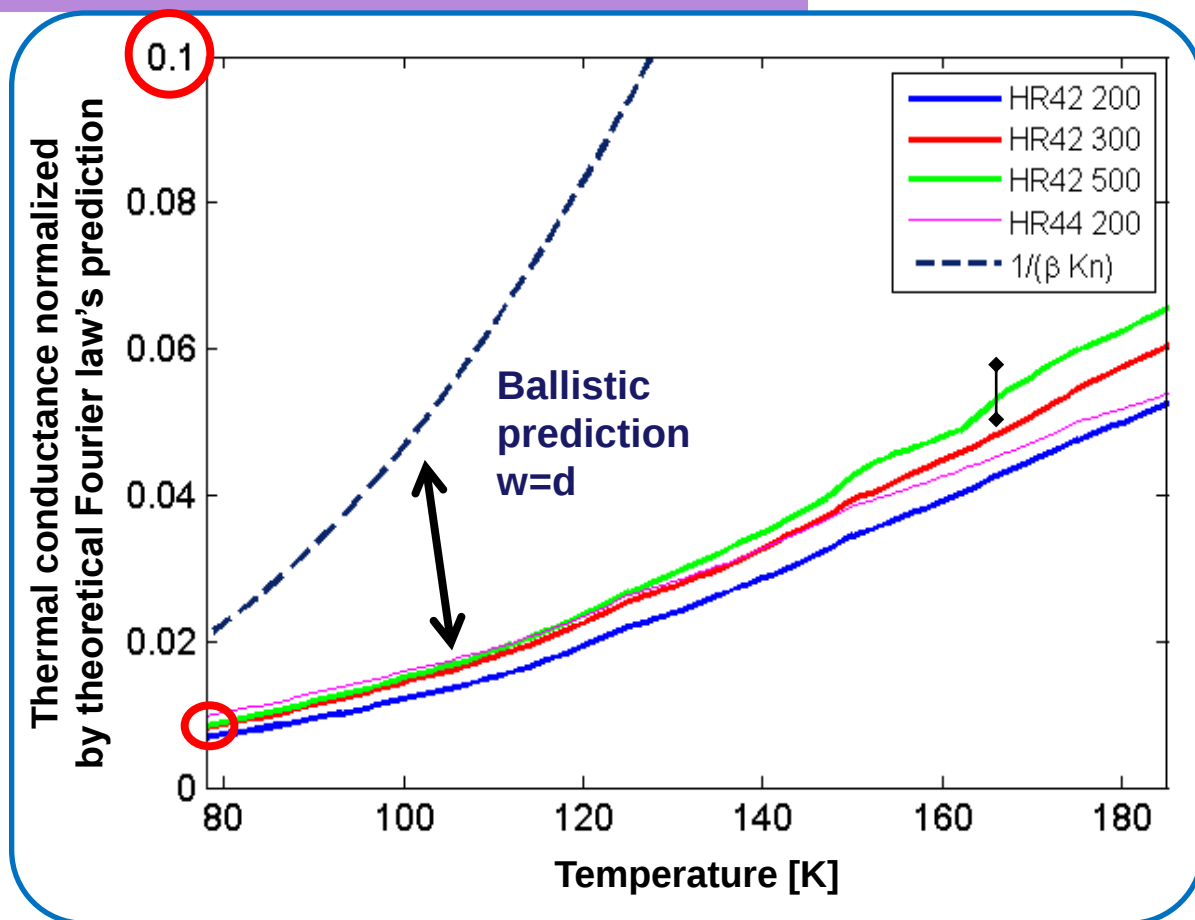
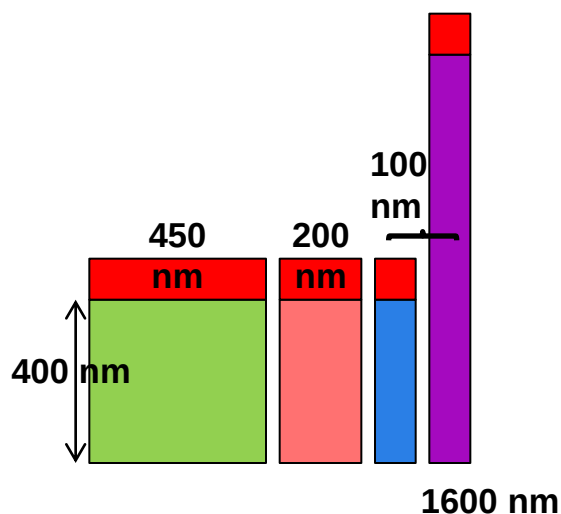


→ G appears to follow a w/d trend (Fourier ?)

Thermal conductances of Si ridges

Deviation from ballistic theory

	3	2	1	4
Ratio $S(\text{cavity})/$ $S(\text{contact})$	2.8	5	9	33

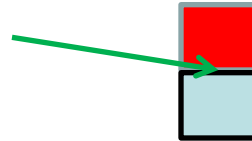


- Far below the Fourier prediction (<10%)
- Different from a pure ballistic prediction (<50%)

Thermal conductances of Si ridges

Why are there deviations from the ballistic theory

1) Surface thermal resistance



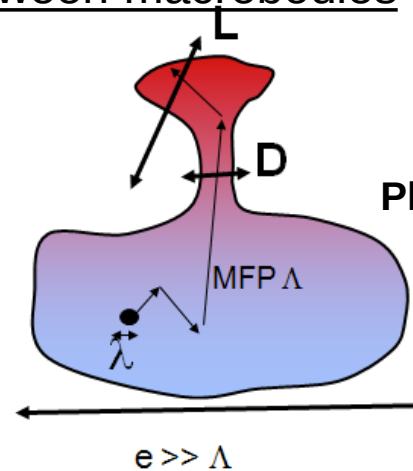
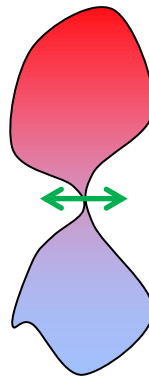
So far not observed with 3ω

2) Correction to theory of constrictions between macrobodies ('Nano' correction)

Ballistic approach

Assumption : two heat baths

All phonons are supposed to be transmitted through the constriction



Phonon backscattering ?

No thermalization in the nanostructure ?

$$R_{th} = R_{Fourier} (1 + \beta Kn) \cdot C(W / BTE) \frac{1}{1 - \gamma}$$

Fourier prediction Ballistic deviation

Wexler's formula

« Nano » correction to Wexler/BTE

BTE correction to Wexler (heat source case)

Volz, JAP (2008)

Conclusion/Perspectives

- The thermal conductance of silicon ridges has been measured for ridges of thickness between 100-450 nm.
 - Its temperature dependence (i.e. Knudsen number) was observed
 - Compared to Fourier law a two orders of magnitude decrease was measured and ascribed to confinement
 - At least one order of magnitude difference with the ballistic transport prediction
-
- Confirmation with other samples using the 3ω method
 - Lower temperatures $\rightarrow$ interplay with strong wave effect
Higher temperatures $\rightarrow$ larger range of Knudsen number
 - Impact of roughness
 - Refinement of the associated theory in progress

Thank you for your attention !
Questions ?